MOSFETs Silicon N-channel MOS (U-MOSIV)

# TK40S10K3Z

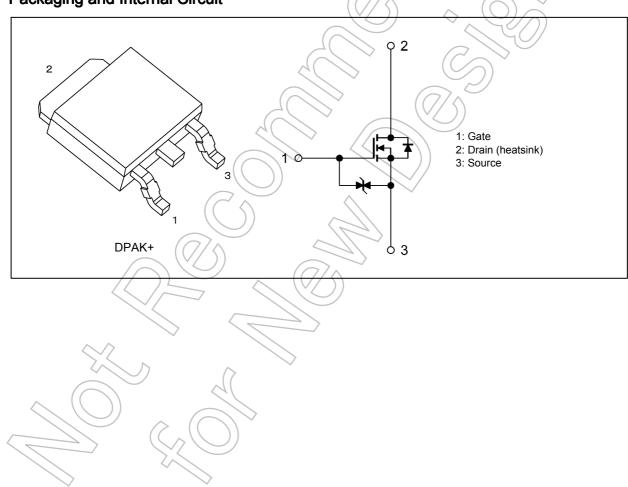
#### 1. Applications

- Automotive
- Motor Drivers
- DC-DC Converters
- Switching Voltage Regulators

#### 2. Features

- (1) AEC-Q101 qualified
- (2) Low drain-source on-resistance:  $R_{DS(ON)} = 14.4 \text{ m}\Omega \text{ (typ.)} (V_{GS} = 10 \text{ V})$
- (3) Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 100 \ V)$
- (4) Enhancement mode:  $V_{th} = 3.0$  to 4.0 V ( $V_{DS} = 10$  V,  $I_D = 1$  mA)

#### 3. Packaging and Internal Circuit



#### 4. Absolute Maximum Ratings (Note) ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristic	3		Symbol	Rating	Unit
Drain-source voltage			V <sub>DSS</sub>	100	V
Gate-source voltage			V <sub>GSS</sub>	±20	
Drain current (DC)		(Note 1)	I <sub>D</sub>	40	A
Drain current (pulsed)		(Note 1)	I <sub>DP</sub>	80	
Power dissipation	(T <sub>c</sub> = 25°C)		PD	93	W
Single-pulse avalanche energy		(Note 2)	E <sub>AS</sub>	98	mJ
Avalanche current			IAR	40	A
Channel temperature		(Note 3)	T <sub>ch</sub>	) 175	°C
Storage temperature		(Note 3)	T <sub>stg</sub>	-55 to 175	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

	Characteristics	6	Symbol	Max	Unit
Channel-to-case thermal resistance	$ \geq \langle \rangle >$	$(\vee)$	R <sub>th(ch-c)</sub>	1.6	°C/W
			/		

Note 1: Ensure that the channel temperature does not exceed 175°C.

Note 2:  $V_{DD}$  = 25 V,  $T_{ch}$  = 25°C (initial), L = 99  $\mu$ H,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 40 A

Note 3: The definitions of the absolute maximum channel and storage temperatures are qualified per AEC-Q101.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

#### 6. Electrical Characteristics

#### 6.1. Static Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±16 V, $V_{DS}$ = 0 V	_	_	±10	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V	$\langle \rangle$		10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	100		—	V
	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	55	$\langle \gamma \rangle$	_	
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	3.0	2_	4.0	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A	/	14.4	18	mΩ

#### 6.2. Dynamic Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	3110	$\langle \downarrow \rangle$	pF
Reverse transfer capacitance	C <sub>rss</sub>			245		
Output capacitance	C <sub>oss</sub>		((	400	_	
Switching time (rise time)	tr	See Figure 6.2.1.	X	22	) —	ns
Switching time (turn-on time)	t <sub>on</sub>		$\sim$	44	_	
Switching time (fall time)	t <sub>f</sub>			13	_	
Switching time (turn-off time)	t <sub>off</sub>			57	_	

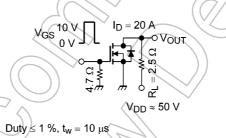


Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 80$ V, $V_{GS}$ = 10 V, $I_D$ = 40 A	_	61	—	nC
Gate-source charge	Q <sub>gs</sub>	$\sim$		36	_	
Gate-drain charge	Q <sub>gd</sub>		_	25	_	

### 6.4. Source-Drain Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	<u>z</u>	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 4)	I <sub>DR</sub>	—	_	_	40	A
Reverse drain current (pulsed)	(Note 4)	I <sub>DRP</sub>	—	_	_	80	
Diode forward voltage		$V_{DSF}$	I <sub>DR</sub> = 40 A, V <sub>GS</sub> = 0 V	—	_	-1.2	V
Reverse recovery time		t <sub>rr</sub>	I <sub>DR</sub> = 40 A, V <sub>GS</sub> = 0 V		58	_	ns
Reverse recovery charge		Q <sub>rr</sub>	-dI <sub>DR</sub> /dt = 50 A/μs	_	58	—	nC

Note 4: Ensure that the channel temperature does not exceed 175°C.

#### TK40S10K3Z

### 7. Marking (Note)

**TOSHIBA** 

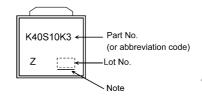
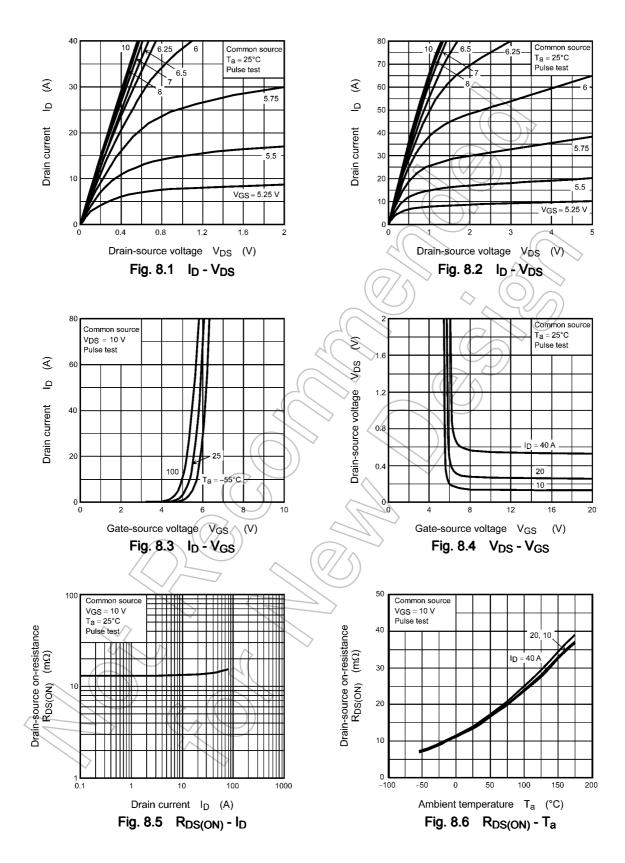
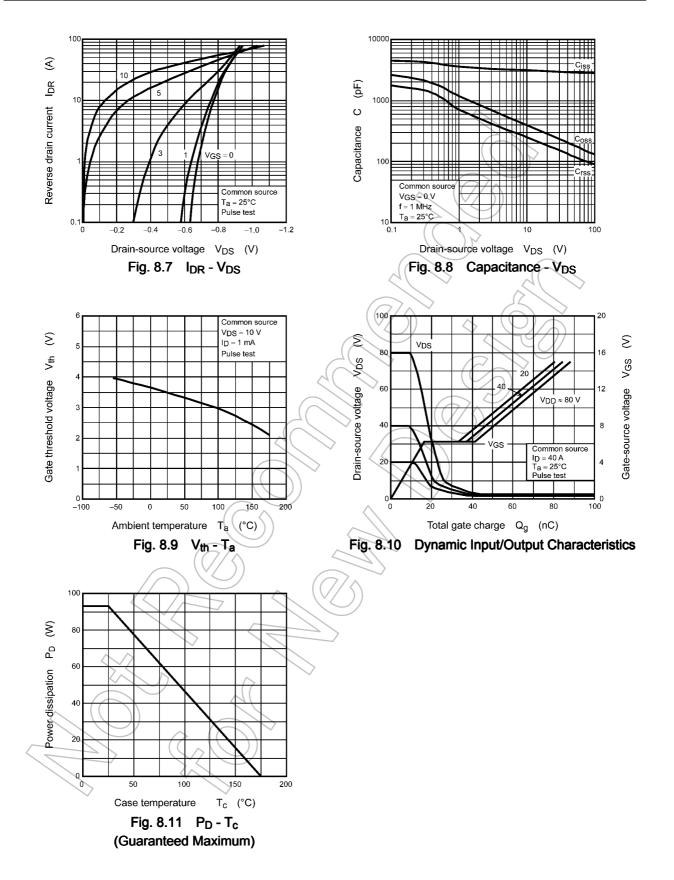


Fig. 7.1 Marking

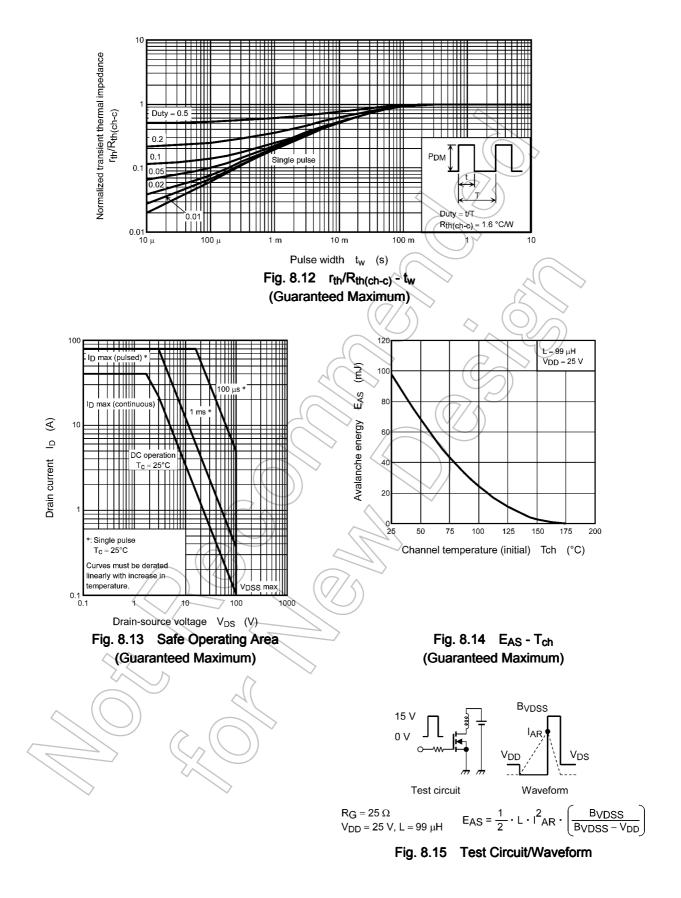
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#### 8. Characteristics Curves (Note)





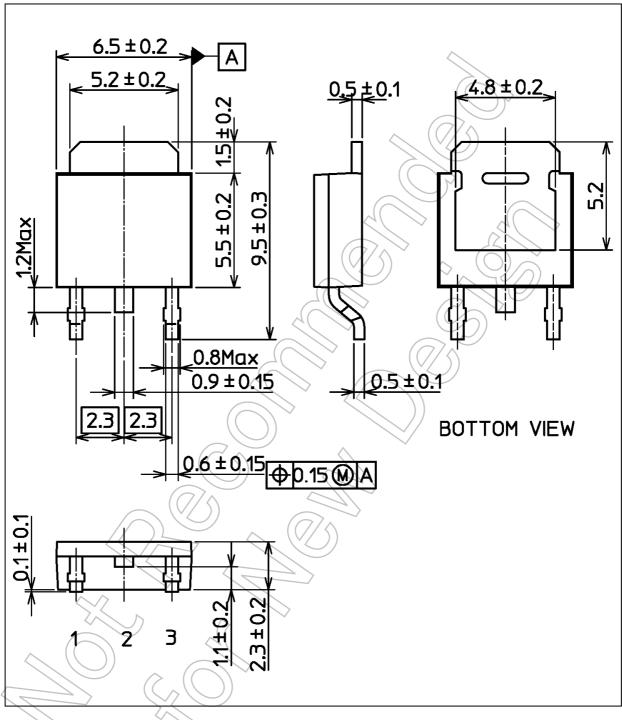




Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Unit: mm



Weight: 0.36 g (typ.)

	Package Name(s)	
TOSHIBA: 2-7M1A		
Nickname: DPAK+		

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